

**AMENDMENTS TO THE SPECIFICATION:**

Please amend the title of the specification as follows:

~~SEMICONDUCTOR DEVICE INCORPORATED THEREIN HIGH k CAPACITOR  
DEIELECTRIC AND METHOD FOR THE MANUFACTURE THEREOF~~ **METHOD FOR  
MANUFACTURING A SEMICONDUCTOR DEVICE FOR USE IN A MEMORY CELL  
THAT INCLUDES FORMING A COMPOSITE LAYER OF TANTALUM OXIDE AND  
TITANIUM OXIDE OVER A BOTTOM CAPACITOR ELECTRODE**

Please amend the paragraph starting at line 2 on page 7 as follows:

In an ensuing step, lower electrodes 125 ~~[[is]]~~ **are** formed on top of the active matrix 110 by using a semiconductor process in such a way that each of the lower electrodes 125 is electrically connected to a corresponding poly plug 116, as shown in Fig. ~~[[1B]]~~ **2B**. It is preferable that the lower electrode 125 is made of a material selected from a group consisting of a poly-Si, W, WN, ~~[[Wsi<sub>x</sub>]]~~ **WSi<sub>x</sub>**, TiN, Pt, Ru, Ir and the like.